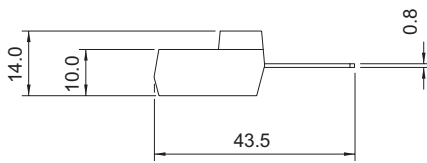
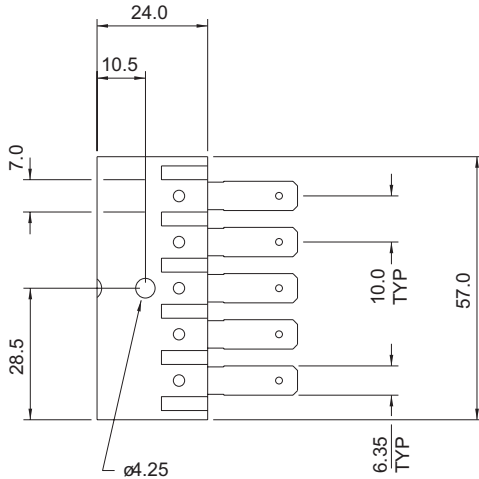


MECHANICAL DATA

Dimensions in mm



CASE 2

SMARTPACK POWER MODULE

POWER MOSFETS FOR AUDIO APPLICATIONS

FEATURES

- P - CHANNEL POWER MOSFETS
- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N - CHANNEL AVAILABLE

ABSOLUTE MAXIMUM RATINGS

(T_{case} = 25°C unless otherwise stated)

		LB32P16	LB32P20
V _{DSX}	Drain – Source Voltage	-160V	-200V
V _{GSS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	- 32A	
I _{D(PK)}	Body Drain Diode	- 32A	
P _D	Total Power Dissipation @ T _{case} = 25°C	500W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	0.3°C/W	

STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX}	Drain – Source Breakdown Voltage	V _{GS} = 10V I _D = -10mA	LB32P16	-160			V
			LB32P20	-200			
BV _{GSS}	Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100µA	±14			V
V _{GS(OFF)}	Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.1		-1.5	V
V _{DS(SAT)*}	Drain – Source Saturation Voltage	V _{GS} = -10V	I _D = -32A			-12	V
I _{DSX}	Drain – Source Cut-Off Current	V _{GS} = 10V	V _{DS} = -160V LB32P16			-10	mA
			V _{DS} = -200V LB32P20			-10	
yfs*	Forward Transfer Admittance	V _{DS} = -10V	I _D = -5A	2		6	S

DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic		Test Conditions	TYP	Unit
C _{iss}	Input Capacitance	V _{DS} = -10V f = 1MHz	P-Ch	pF
			TBE	
			TBE	
C _{oss}	Output Capacitance	V _{DS} = -20V I _D = -7A	TBE	ns
C _{rss}	Reverse Transfer Capacitance		TBE	
t _{on}	Turn-on Time	V _{DS} = -20V I _D = -7A	TBE	ns
t _{off}	Turn-off Time		TBE	

* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.

